

HiPerFRED

V_{RRM} = 600V
 I_{FAV} = 2x 15A
 t_r = 35ns

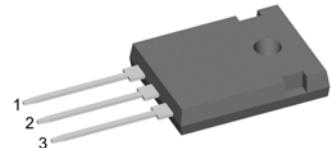
High Performance Fast Recovery Diode

Low Loss and Soft Recovery

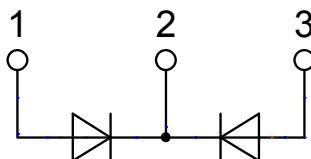
Common Cathode

Part number

DSEC30-06A



Backside: cathode

**Features / Advantages:**

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-247

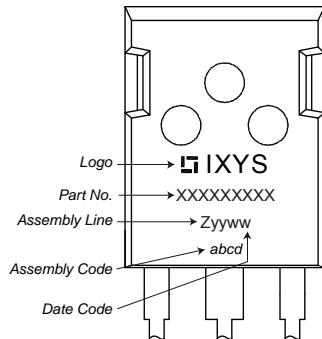
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Fast Diode

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			600	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			600	V
I_R	reverse current, drain current	$V_R = 600 V$ $V_R = 600 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		100 0.5	μA mA
V_F	forward voltage drop	$I_F = 15 A$ $I_F = 30 A$ $I_F = 15 A$ $I_F = 30 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		2.03 2.24 1.34 1.57	V V V V
I_{FAV}	average forward current	$T_C = 140^\circ C$ rectangular $d = 0.5$	$T_{VJ} = 175^\circ C$		15	A
V_{FO} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 175^\circ C$		0.99 14.3	V mΩ
R_{thJC}	thermal resistance junction to case				1.6	K/W
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		95	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}; V_R = 0 V$	$T_{VJ} = 45^\circ C$		110	A
C_J	junction capacitance	$V_R = 400 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$		12	pF
I_{RM}	max. reverse recovery current		$T_{VJ} = 25^\circ C$		5	A
t_{rr}	reverse recovery time	$I_F = 15 A; V_R = 300 V$ $-di_F/dt = 200 A/\mu s$	$T_{VJ} = 100^\circ C$ $T_{VJ} = 25^\circ C$ $T_{VJ} = 100^\circ C$		7 35 95	A ns ns
E_{AS}	non-repetitive avalanche energy	$I_{AS} = 1 A$ $L = 180 \mu H$	$T_{VJ} = 25^\circ C$		0.1	mJ
I_{AR}	repetitive avalanche current	$V_A = 1.5 \cdot V_R$ typ.: $f = 10 \text{ kHz}$			0.1	A

Package TO-247			Ratings		
Symbol	Definition	Conditions	min.	typ.	max.
		per terminal ¹⁾			Unit
I_{RMS}	RMS current	per terminal ¹⁾			50 A
T_{VJ}	virtual junction temperature		-55		175 °C
T_{op}	operation temperature		-55		150 °C
T_{stg}	storage temperature		-55		150 °C
Weight				6	g
M_D	mounting torque		0.8		1.2 Nm
F_c	mounting force with clip		20		120 N

Product Marking



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEC30-06A	DSEC30-06A	Tube	30	473502

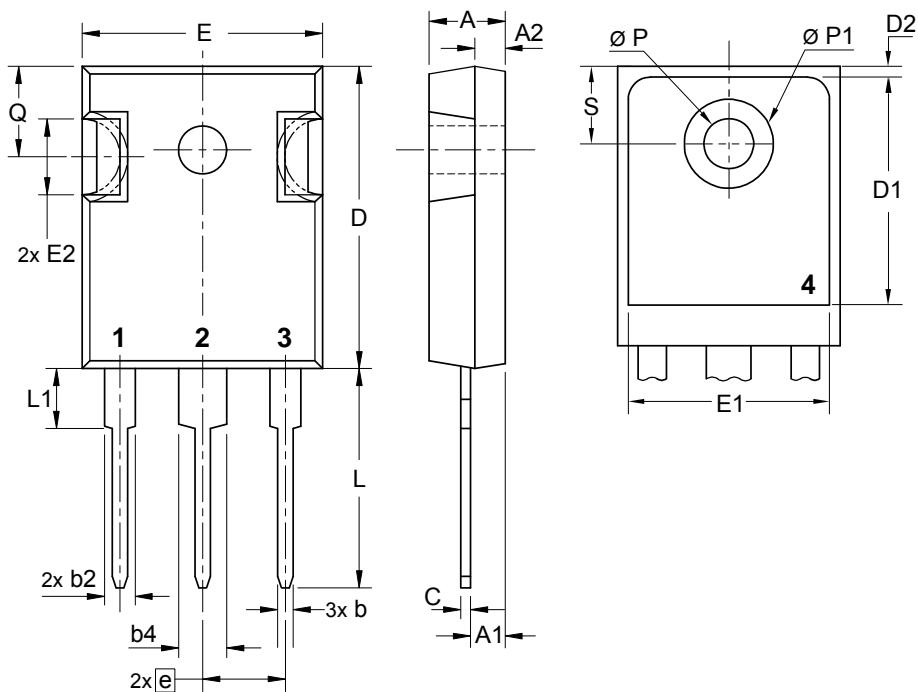
Similar Part	Package	Voltage class
DSEC30-06B	TO-247AD (3)	600
DSEC29-06AC	ISOPLUS220AB (3)	600

Equivalent Circuits for Simulation

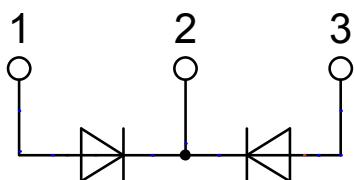
^{*} on die level $T_{VJ} = 175 \text{ }^{\circ}\text{C}$

	Fast Diode
$V_{0\max}$	threshold voltage
$R_{0\max}$	slope resistance *

Outlines TO-247



Sym.	Inches min. max.	Millimeter min. max.
A	0.185 0.209	4.70 5.30
A1	0.087 0.102	2.21 2.59
A2	0.059 0.098	1.50 2.49
D	0.819 0.845	20.79 21.45
E	0.610 0.640	15.48 16.24
E2	0.170 0.216	4.31 5.48
e	0.215 BSC	5.46 BSC
L	0.780 0.800	19.80 20.30
L1	- 0.177	- 4.49
Ø P	0.140 0.144	3.55 3.65
Q	0.212 0.244	5.38 6.19
S	0.242 BSC	6.14 BSC
b	0.039 0.055	0.99 1.40
b2	0.065 0.094	1.65 2.39
b4	0.102 0.135	2.59 3.43
c	0.015 0.035	0.38 0.89
D1	0.515 -	13.07 -
D2	0.020 0.053	0.51 1.35
E1	0.530 -	13.45 -
Ø P1	- 0.29	- 7.39



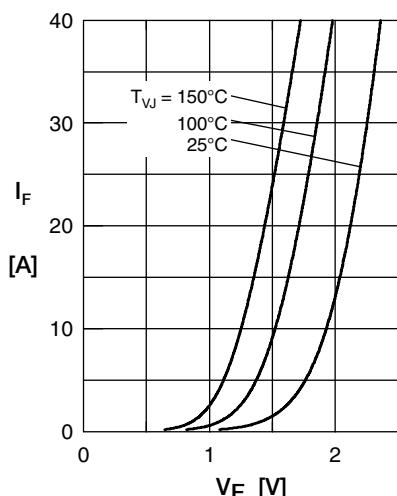
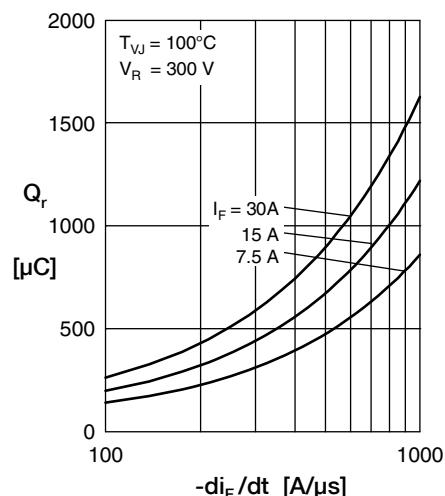
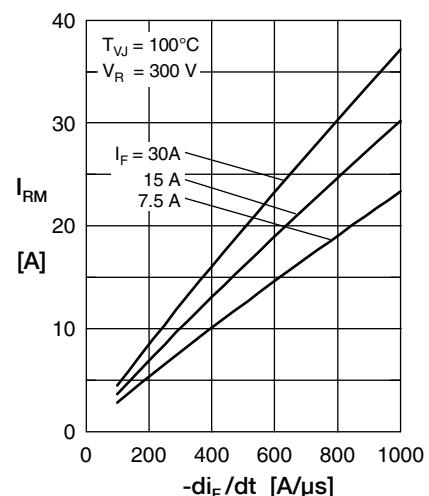
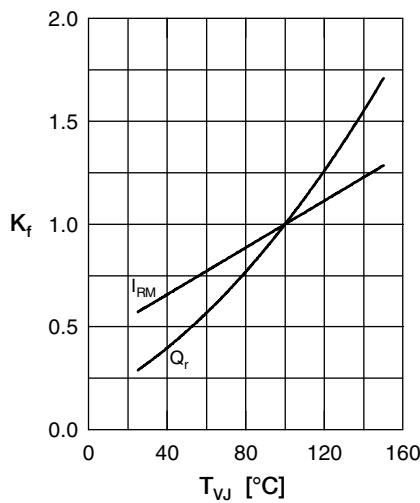
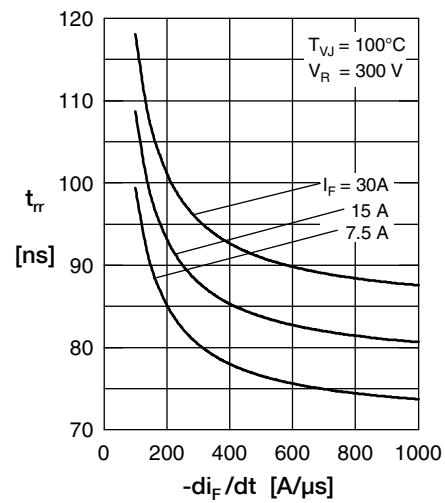
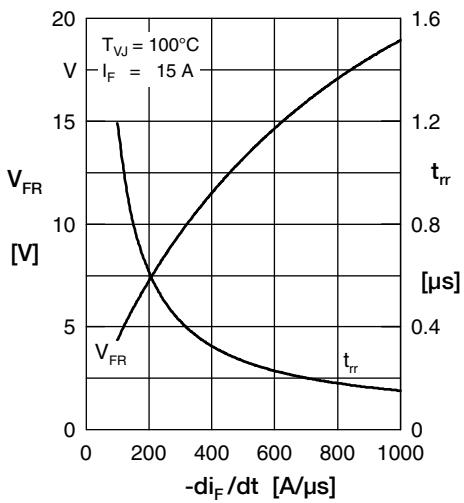
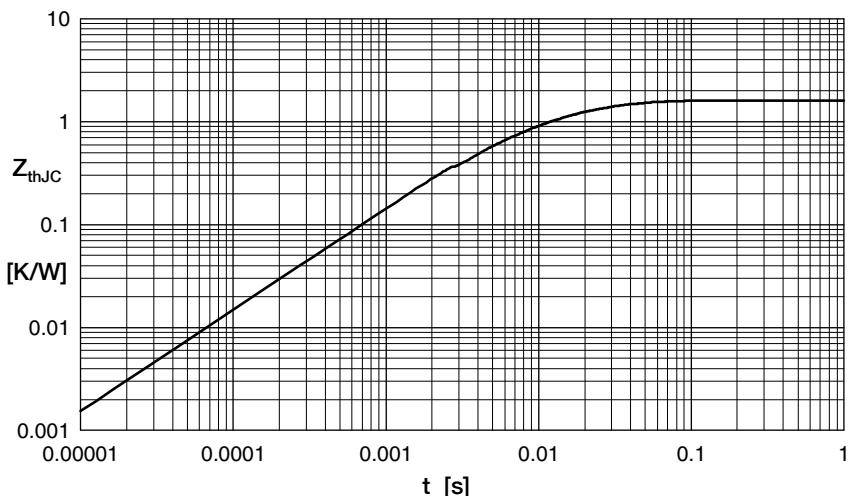
Fast DiodeFig. 1 Forward current I_F versus V_F Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$ Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$ Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ} Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$ Fig. 6 Typ. peak forward voltage V_{FR} and t_{rr} versus di_F/dt 

Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.908	0.0052
2	0.350	0.0003
3	0.342	0.017